

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TH430** is Designed for SSB and VHF communications. This device utilizes emitter ballasting for improved ruggedness and reliability.

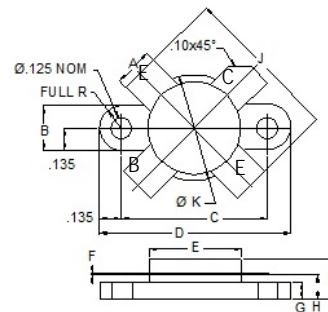
FEATURES:

- $P_G = 14.5$ dB min. at 220 W/30 MHz
- $IMD = -30$ dB max.
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	40 A
V_{CBO}	110 V
V_{CEO}	55 V
V_{EBO}	4.0 V
P_{DISS}	330 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$0.40^\circ C/W$

PACKAGE STYLE 0.550 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.225 / 5.72	.235 / 5.97
B	.265 / 6.73	.275 / 6.96
C	.880 / 21.84	.870 / 22.10
D	1.130 / 28.70	1.140 / 28.96
E	.545 / 13.84	.555 / 14.10
F	.003 / 0.08	.007 / 0.18
G	.098 / 2.49	.118 / 3.00
H	.150 / 3.81	.170 / 4.32
I		.280 / 7.11
J	1.080 / 27.43	1.120 / 28.45
K	.625 / 15.88	.635 / 16.13

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200$ mA	55			V
BV_{CES}	$I_C = 200$ mA	110			V
BV_{EBO}	$I_E = 20$ mA	4.0			V
I_{CEO}	$V_{CE} = 30$ V			10	mA
I_{CES}	$V_{CE} = 60$ V			10	mA
h_{FE}	$V_{CE} = 6.0$ V $I_C = 10$ A	15		80	---
C_{ob}	$V_{CB} = 50$ V $f = 1.0$ MHz		320	360	pF
G_P	$V_{CE} = 50$ V $I_{CQ} = 150$ mA $f = 30$ MHz	14.5			dB
IMD_3	$P_{OUT} = 250$ W (PEP)			-30	dBc
η_c		37			%